

L Number	Hits	Search Text	DB	Time stamp
-	0	(ITO same mylar) and silsesquioxane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/13 12:01
-	1842	silsesquioxane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 08:18
-	0	(silsesquioxane and mylar) and (ito or (indium adj tin adj oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/30 11:58
-	73	silsesquioxane and (plastic same substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/30 12:53
-	2	(silsesquioxane and (plastic same substrate)) and (ito or (indium adj tin adj oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/30 11:58
-	295	silsesquioxane and precursor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/30 12:54
-	42	silsesquioxane and (precursor same alkyl)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/30 12:58
-	3	silsesquioxane and (precursor same (alkyl adj methyl))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/30 12:59
-	8	silsesquioxane and mylar	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/30 13:08
-	0	(ITO same mylar) and hsq	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/30 13:08
-	112	ITO same mylar	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/30 13:19
-	22	silsesquioxane same gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/30 13:21

	2111	silsesquioxane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 11:20
	1143	silsesquioxane and organic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 11:20
	22	(silsesquioxane and organic) and (FET or (field adj effect adj transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 11:21
	153	(silsesquioxane and organic) and (FET or (field adj effect adj transistor) or transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 11:21
	197	silsesquioxane and (low adj temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 11:22
	19	(silsesquioxane and (low adj temperature)) and ((low adj temperature) same cure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 11:53
	178	(silsesquioxane and (low adj temperature)) not ((silsesquioxane and (low adj temperature)) and ((low adj temperature) same cure))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 12:38
	2	("6066574").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 12:54
	112	((silsesquioxane and organic) and (FET or (field adj effect adj transistor) or transistor)) not ((silsesquioxane and (low adj temperature)) not ((silsesquioxane and (low adj temperature)) and ((low adj temperature) same cure)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 12:54
	111	((((silsesquioxane and organic) and (FET or (field adj effect adj transistor) or transistor)) not ((silsesquioxane and (low adj temperature)) not ((silsesquioxane and (low adj temperature)) and ((low adj temperature) same cure)))) not (silsesquioxane and (low adj temperature)) tft and silsesquioxane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 12:54
	8		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 18:31
	11	organic adj fet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 18:31

	2112	silsesquioxane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 08:18
	461	silsesquioxane and cure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 09:49
	244	silsesquioxane and (cure same (temperature or degrees or degree))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 08:43
	3	("5384376").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 09:28
	3	("5500537").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 09:28
	17	silsesquioxane same precursor same (cure or cured or curing) same (temperature or temp)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/08/25 09:30
	74	silsesquioxane same precursor and ((cure or cured or curing) same (temperature or temp))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/08/25 11:11
	57	(silsesquioxane same precursor and ((cure or cured or curing) same (temperature or temp))) not (silsesquioxane same precursor same (cure or cured or curing) same (temperature or temp))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/08/25 09:31
	598	silsesquioxane and ((cure or cured or curing) same (temperature or temp))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/08/25 11:11
	476	silsesquioxane and ((cure or cured or curing) with (temperature or temp))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/08/25 11:12
	149	silsesquioxane and ((precursor or resin) same ((cure or cured or curing) with (temperature or temp)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/08/25 11:13
	1	("6156743").PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/08/25 12:01
	1	("6472076").PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/08/25 12:01
	8	(organic adj fet) with substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/13 12:08

	1	("20020136910").PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 12:08
	1	silsesquioxane and (phenyl adj pendant adj group)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 09:50
	4	silsesquioxane and (phenyl adj pendant)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 09:50
	979	silsesquioxane and (phenyl)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 11:45
	158	silsesquioxane and (phenyl) and oligomer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 09:51
	40	silsesquioxane and (phenyl same oligomer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 10:14
	31	silsesquioxane and (phenyl same precursor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 10:42
	53	silsesquioxane and (phenyl same precursor\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 10:42
	22	(silsesquioxane and (phenyl same precursor\$)) not (silsesquioxane and (phenyl same precursor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 10:47
	0	silsequioxane same precursor same phenyl	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 10:48
	1	silsequioxane same precursor\$ same phenyl	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 11:17
	6	(GR150 or GR710 or GR720P) and silsesquioxane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 11:22

-	13	(GR150 or GR710 or GR720P)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 11:22
-	7	((GR150 or GR710 or GR720P)) not ((GR150 or GR710 or GR720P) and silsesquioxane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 11:24
-	52	gate same silsesquioxane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 12:08
-	309	silsesquioxane same phenyl	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 11:45
-	11	(silsesquioxane same phenyl) and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 11:49
-	43	(silsesquioxane same phenyl) same dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 12:01
-	29	silsesquioxane same gate same dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 12:05
-	1	("6251486").PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/08/06 12:05
-	18	gate with silsesquioxane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 12:08
-	44	gate with (silsesquioxane or HSQ)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 12:14
-	3364	organic adj semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 12:15
-	611	(organic adj semiconductor) and gate and source and drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 12:17

	0	((organic adj semiconductor) and gate and source and drain) and silsesquioxane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 12:17
	219	((organic adj semiconductor) and gate and source and drain) and (gate with dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 12:16
	3	((organic adj semiconductor) and gate and source and drain) and (substrate same (polyethylene adj terphthalate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 12:20
	0	((organic adj semiconductor) and gate and source and drain) and (substrate same (indium adj tin adj oxide))) and (polyethylene adj terphthalate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 12:21
	97	((organic adj semiconductor) and gate and source and drain) and (substrate same (indium adj tin adj oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 12:23
	5	((organic adj semiconductor) and gate and source and drain) and (substrate same (indium adj tin adj oxide))) and mylar	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/06 12:23